UPG15N60E

**Preliminary** 

Insulated Gate Bipolar Transistor

# 600V, SMPS N-CHANNEL IGBT

#### DESCRIPTION

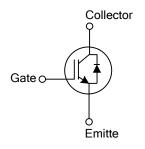
The UTC **UPG15N60E** is a N-channel IGBT. it uses UTC's advanced technology to provide customers with high input impedance, high switching speed and low conduction loss, etc.

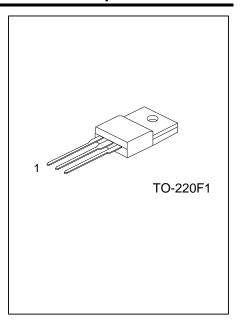
The UTC **UPG15N60E** is suitable for high voltage switching, high frequency switch mode power supplies.

#### ■ FEATURES

- \*  $V_{CE(SAT)} \le 2.3V$  @  $I_C=15A$ ,  $V_{GE}=15V$
- \* High switching speed
- \* High input impedance
- \* Low conduction loss

#### ■ SYMBOL





#### **■ ORDERING INFORMATION**

Ordering Number		Daalaasa	Pin Assignment			Daaldaa	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UPG15N60EL-TF1-T	UPG15N60EG-TF1-T	TO-220F1	G	С	Е	Tube	

Note: Pin Assignment: G: Gate C: Collector E: Emitter

UPG15N60EG-TF1-T (1)Packing Type (1) T: Tube

(2)Package Type (2) TF1: TO-220F1 (3)Green Package (3) G: Halogen Free and Lead Free, L: Lead Free

### **■ MARKING**



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# ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		$V_{CES}$	600	V
Gate to Emitter Voltage Continuous		$V_{GES}$	±20	V
Continuous Collector Current	T <sub>C</sub> =25°C	_	30	Α
	T <sub>C</sub> =100°C	Ic	15	Α
Collector Current Pulsed (Note 2)		I <sub>CM</sub>	4.5	Α
O-milionary Famoural Original	T <sub>C</sub> =25°C		15	Α
Continuous Forward Current	T <sub>C</sub> =100°C	l <sub>F</sub>	7.5	Α
Forward Current Pulsed		I <sub>FM</sub>	104	Α
Peak Diode Recovery dv/dt (Note 3)		dv/dt	6.7	V/ns
Power Dissipation		$P_{D}$	30	W
Junction Temperature		$T_J$	-55 ~ +150	°C
Storage Temperature Range		$T_{STG}$	-55 ~ <b>+</b> 150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3.  $I_F \le 15A$ , di/dt  $\le 200A/\mu s$ ,  $V_{CC} \le BV_{CES}$ , Starting  $T_J = 25$ °C

## **THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	$\theta_{JC}$	4.17	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	I <sub>C</sub> =250μA, V <sub>GE</sub> =0V					V
Collector-Emitter Leakage Current	I <sub>CES</sub>	V <sub>CE</sub> =600V, V <sub>GE</sub> =0V				10	μΑ
Gate to Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V				±400	nA
ON CHARACTERISTICS							
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	1 450 \/ 45\/	T <sub>J</sub> =25°C		1.8	2.3	V
		I <sub>C</sub> =15A, V <sub>GE</sub> =15V	T <sub>J</sub> =150°C		2.0		V
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	$I_C=250\mu A, V_{CE}=V_{GE}$		4.0		6.5	V
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>IES</sub>	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V, f=1MHz			527		pF
Output Capacitance	C <sub>OES</sub>				71		pF
Reverse Transfer Capacitance	C <sub>RES</sub>				11		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge	$Q_{G}$				19		nC
Gate-Emitter Charge	$Q_{GE}$	I <sub>C</sub> =15A, V <sub>CE</sub> =100V, V <sub>GE</sub> =10V			5		nC
Gate-Collector Charge	$Q_{GC}$	]			7.5		nC
Current Turn-On Delay Time	t <sub>D(ON)</sub>				54.7		ns
Current Rise Time	t <sub>R</sub>	I <sub>C</sub> =15A, V <sub>CE</sub> =50V, V <sub>GE</sub> =15V,			50		ns
Current Turn-Off Delay Time	t <sub>D(OFF)</sub>	R <sub>G</sub> =10Ω			51		ns
Current Fall Time	t <sub>F</sub>				52		ns
DRAIN-SOURCE DIODE CHARACTER	ISTICS	4	B, 120	U			
Forward Voltage Drop	$V_{FM}$	I <sub>F</sub> =6A				2.2	V
Reverse Recovery Time	t <sub>rr</sub>	1 -64 41/4+ 4504/464	(0-400V		72		ns
Reverse Recovery Charge	Qrr	I <sub>F</sub> =6A, dl/dt=150A/μS, V <sub>CC</sub> =400V			150		nC
Note: Pulse Test: Pulse width ≤ 50 µs.		SOFT POLITICES					
	3	Partilla					
Reverse Recovery Charge $Q_{rr}$ $I_F=6A$ , $dVdt=150A/\mu S$ , $V_{CC}=400V$ 150 nC Note: Pulse Test: Pulse width $\leq 50\mu s$ .							
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#### **■ TEST CIRCUIT AND WAVEFORMS**

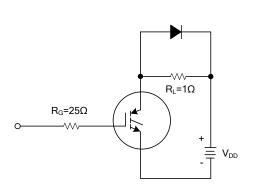


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

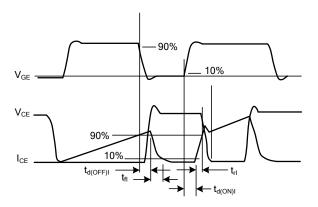


Fig 2. SWITCHING TEST WAVEFORMS

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